

General Description:

The high breakdown voltage, fast switching speed and high forward conductance of this diode packaged in a DO-35 miniature Glass Axial leaded package makes it desirable also as a general purpose diode.

High Conductance Fast Diode

Features:

- 500 milliwatt Power Dissipation package.
- Fast Switching Speed,
- Typical capacitance less than 1.0 picofarad.

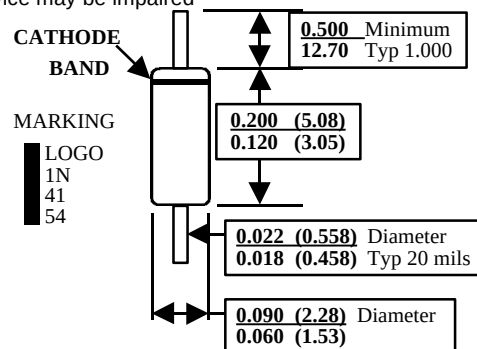
Ordering:

- 13 inch reel, 50 mm (T50R) & 26 mm (T26R) Tape; 10,000 units per reel.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Sym	Parameter	Value	Units
T _{stg}	Storage Temperature	-65 to +200	°C
T _j	Operating Junction Temperature	175	°C
P _D	Total Power Dissipation at T _A = 25°C	500	mW
	Linear Derating Factor from T _A = 25°C	3.33	mW/°C
R _{OJA}	Thermal Resistance Junction-to-Ambient	300	°C/W
W _{iv}	Working Inverse Voltage	35	V
I _O	Average Rectified Current	100	mA
I _F	DC Forward Current (I _F)	300	mA
i _f	Recurrent Peak Forward Current (I _F)	400	mA
i _{F(surge)}	Peak Forward Surge Current (I _{FSM}) Pulse Width = 1.0 second	1.0	Amp
	Pulse Width = 1.0 microsecond	4.0	Amp

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired



Electrical Characteristics TA = 25°C unless otherwise noted

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B _V	Breakdown Voltage	35		V	I _R = 5.0 uA
I _R	Reverse Leakage		100 100	nA uA	V _R = 25 V V _R = 25 V, T _A = 150°C
V _F	Forward Voltage		1.0	V	I _F = 30 mA
C _T	Capacitance		4.0	pF	V _R = 0.0 V, f = 1.0 MHz
T _{RR}	Reverse Recovery Time		4.0	ns	I _F = 10 mA V _R = 6.0 V I _{RR} = 1.0 mA, R _L = 100 ohms